

AMENDMENT

SERIAL NO.: 09/321,605

forming an upper electrode of the capacitor on the oxide dielectric film;  
forming a second insulating film for covering the capacitor;  
forming a first opening for electrically connecting the impurity diffusion layer and a second opening which exposes the upper electrode in the first and second insulating films, by etching a part of the second insulating film and a part of the first insulating film;  
forming a metal film on the second insulating film for connecting electrically the impurity diffusion layer via the first opening and the upper electrode via the second opening;  
forming a local interconnection covering an entire portion of the upper electrode with an area which is larger than an area where the upper electrode contacts with the oxide dielectric film in a plan view, in a range which passes through the first opening and the second opening, by patterning the metal film; and  
forming a third insulating film for covering the local interconnection.

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2. (Twice Amended) A method of manufacturing a semiconductor device according to claim 1, wherein a metal film constituting the local interconnection is formed of metal nitride.

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14. (Twice Amended) A method of manufacturing a semiconductor device according to claim 1 further comprising the step of:

forming a conductive plug between the metal film and the impurity diffusion layer in the first opening.

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21. (Twice Amended) A method of manufacturing a semiconductor device comprising the steps of :

forming an impurity diffusion layer in a semiconductor substrate;

forming a first insulating film covering the semiconductor substrate;

forming a lower electrode of a capacitor on the first insulating film;

forming an oxide dielectric film of the capacitor on the lower electrode;

forming an upper electrode of the capacitor on the oxide dielectric film;

forming a second insulating film for covering the capacitor;

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forming a first opening for electrically connecting the impurity diffusion layer and a second opening which exposes the upper electrode in the first and second insulating films, by etching a part of the second insulating film and a part of the first insulating film;

forming a metal film on the second insulating film for connecting electrically the impurity diffusion layer via the first opening and the upper electrode via the second opening;

forming a local interconnection covering an entire portion of the upper electrode with an area which is larger than an area where the upper electrode contacts with the oxide dielectric film in a plan view, in a range which passes through the first opening and the second opening, by patterning the metal film, wherein the local interconnection is a blocking layer for preventing a diffusion of a redundant to the oxide dielectric film; and

forming a third insulating film for covering the local interconnection.

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Add new claim 22 as follow:

22. The method of manufacturing a semiconductor device according to claim 1, wherein the local interconnection is formed with surrounding and protruding portions having a fixed size from edges of the area where the upper electrode contacts with the oxide dielectric film.